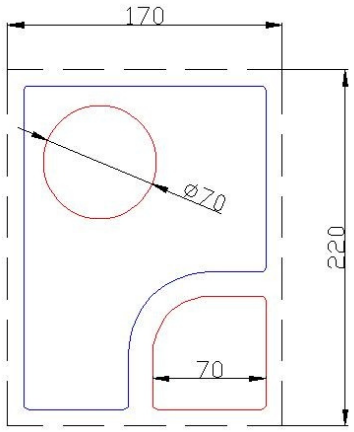
InGaN Blue Chip
Model NO.: NEPTUNE-07A



General Description:

(1) Chip Dimension
Chip Size= 6 ㎜ x 8 ㎜ (170um x 220um)
Chip Thickness = 90±10 μm
P/N Bonding Pad = 70±5 μm
(2) Electrode:
P (Anode) → Au
N (Cathode) → Au
(3) Structure:
Refer to drawing
SiO_2 Passivated surface

Electro-optical Characteristics(Ta=RT)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	V_F	2.7	-	3.0	V	I_F= 5mA
Dominant Wavelength	λ_D	450	-	470	nm	I_F= 5mA
Reverse Current	IR	0	-	2	μA	V_R=-5V

亮度 Lunimous Intensity(I_V) mcd at I_F=5mA	波長 Dominant Wavelength(nm)								
Range	447.5~450	450~452.5	452.5~455	455~457.5	457.5~460	460~462.5	462.5~465	465~467.5	467.5~470
5~10									
10~15	K07AB44DB	K07AB45AB	K07AB45BB						
15~20	K07AB44DC	K07AB45AC	K07AB45BC	K07AB45CC	K07AB45DC	K07AB46AC			
20~25		K07AB45AD	K07AB45BD	K07AB45CD	K07AB45DD	K07AB46AD	K07AB46BD	K07AB46CD	K07AB46DD
25~30					K07AB45DE	K07AB46AE	K07AB46BE	K07AB46CE	K07AB46DE
30~35							K07AB46BF	K07AB46CF	K07AB46DF
35~40									K07AB46DG

Features:

1. High Luminous Intensity
2. Long Operation Life
3. High Current; Pulse Operation
4. Indoor/Outdoor Applications

Notes:

1. Dominant wavelength includes an error of ± 1nm
2. Luminous intensity includes an error of ±10%
3. Luminous intensity is measured on bare chip
4. InGaN LED is sensitive to ESD